# **IV Curves Status**

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### Bias & Trim: digital-voltage conversion

Each AFE of DAPHNE provides bias to 8 PDS channels through 2 DB15 connectors.

Among the 8 channels, we can just fine-tuning the SiPMs' bias with the Trim (0 - 4.096V) -> FBK and HPK SiPM on different AFEs.

 $DAC = V_{bias} * 25.43$ 

TRIM: V\_trim = DACt \* 0.001

## State of the art and aim

We have scripts to read all channels of an endpoint (daphne) performing a coarse scan with the bias and a fine scan with the trim

Next steps:

- automatic loop on all the endpoints
- comparison with expectation values
- warm/cold problem

Aim: ensure that we have good data (as many as possible!) for future analyses



#### Examples



SiPM bias is given by AFE bias - ch. trim

#### Methods

The second derivative method give a V\_bd estimate lower (ref. our preliminary analysis and literature)

Second derivative maximum

Derivative of the logarithm



# Filling problem (?)

During the filling we want to perform Vbd and DCR studies as a function of temperature, however, we will have modules inside and outside the LAr connected to the same AFE

The V\_bd strongly depend on the temperature

e.g. FBK room T = 32.7V

FBK LAr = 27.0V

The must avoid to bias the sensors in cold over a certain threshold -> trim on the SiPMs above the LAr level





#### **Possible solution**

- We can just set up one BIAS for each AFE, however, the trim is set per channel;

- Right now we have a draft of a script which identifies a variation of the current during the IV acquisition and sends a trim information to the channel reducing the BIAS on it.

- We will need feedback from the analysis teams to fix the Vbd for each channel. We will populate the table as soon as possible with the estimated Vbd for each facility.